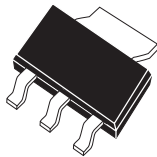


CZT4033

PNP SILICON TRANSISTOR



SOT-223 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZT4033 type is an PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high current general purpose amplifier applications.

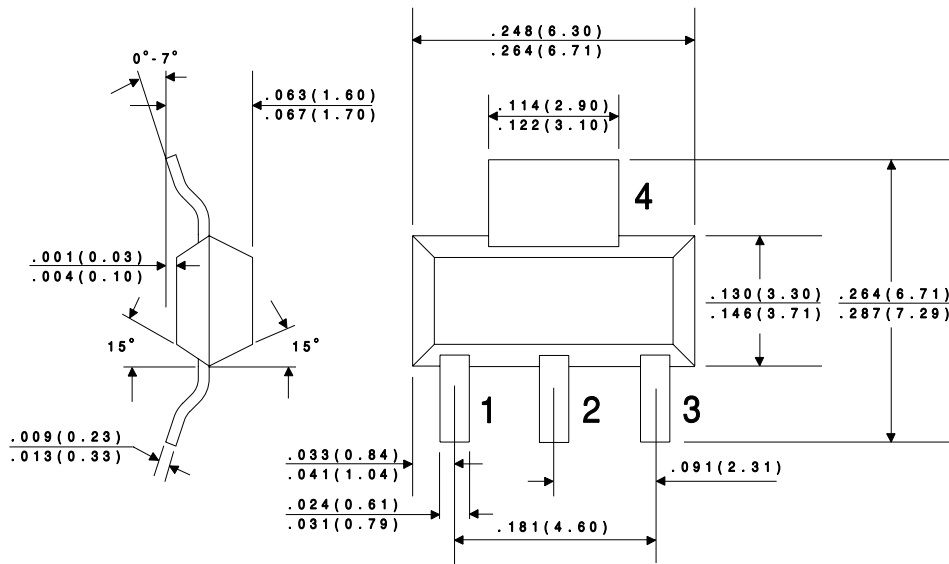
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	1.0	A
Collector Current (Peak)	I_{CM}	1.5	A
Power Dissipation	P_D	2.0	W
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	62.5	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=60\text{V}$		50	nA
I_{EBO}	$V_{EB}=5.0\text{V}$		10	nA
BV_{CBO}	$I_C=10\mu\text{A}$	80		V
BV_{CEO}	$I_C=10\text{mA}$	80		V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.15	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		0.50	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.90	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.10	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=0.1\text{mA}$	75		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$	100	300	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=500\text{mA}$	70		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{A}$	25		
f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=1.0\text{MHz}$	100		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		20	pF
C_{ib}	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		110	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR